# NSB1706DMW5T1

# Dual Bias Resistor Transistor

# NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the NSB1706DMW5T1, two BRT devices are housed in the SC–88A package which is ideal for low power surface mount applications where board space is at a premium.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Pb–Free Package is Available

#### MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted, common for } Q_1 \text{ and } Q_2)$ 

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current	Ι <sub>C</sub>	100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P <sub>D</sub>	187 (Note 1) 256 (Note 2) 1.5 (Note 1) 2.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	670 (Note 1) 490 (Note 2)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P <sub>D</sub>	250 (Note 1) 385 (Note 2) 2.0 (Note 1) 3.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	493 (Note 1) 325 (Note 2)	°C/W
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	188 (Note 1) 208 (Note 2)	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

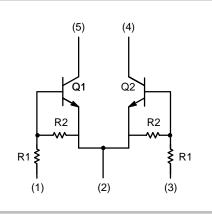
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. FR-4 @ Minimum Pad.

2. FR-4 @ 1.0 x 1.0 inch Pad.



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SC-88A CASE 419A STYLE 1

### MARKING DIAGRAM



U6 = Device Marking M = Date Code • = Pb-Free Package to Mandat may be in either location

#### (Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NSB1706DMW5T1	SC-88A	3000/Tape & Reel
NSB1706DMW5T1G	SC-88A (Pb-Free)	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

<sup>1.</sup> FR-4 @ Minimum Pad.

## NSB1706DMW5T1

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·				
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	-	_	100	nAdc
Collector-Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	-	_	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0 \text{ V}, I_C = 0$ )	I <sub>EBO</sub>	-	-	0.18	mAdc
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu\text{A}, I_E = 0)$	V <sub>(BR)CBO</sub>	50	-	_	Vdc
Collector-Emitter Breakdown Voltage (Note 3) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V <sub>(BR)CEO</sub>	50	-	-	Vdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ( $V_{CE}$ = 10 V, I <sub>C</sub> = 5.0 mA)	h <sub>FE</sub>	80	200	-	
Collector-Emitter Saturation Voltage $(I_C = 10 \text{ mA}, I_B = 1 \text{ mA})$	V <sub>CE(sat)</sub>	-	-	0.25	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	_	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}, \text{ V}_{B} = 0.25 \text{ V}, \text{ R}_{L} = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	_	_	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R1/R2	0.055	0.1	0.185	

3. Pulse Test: Pulse Width < 300  $\mu$ s, Duty Cycle < 2.0%.

NOTE: New resistor combinations. Updated curves to follow in subsequent data sheets.

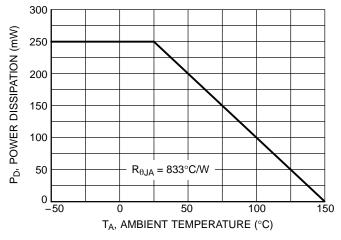
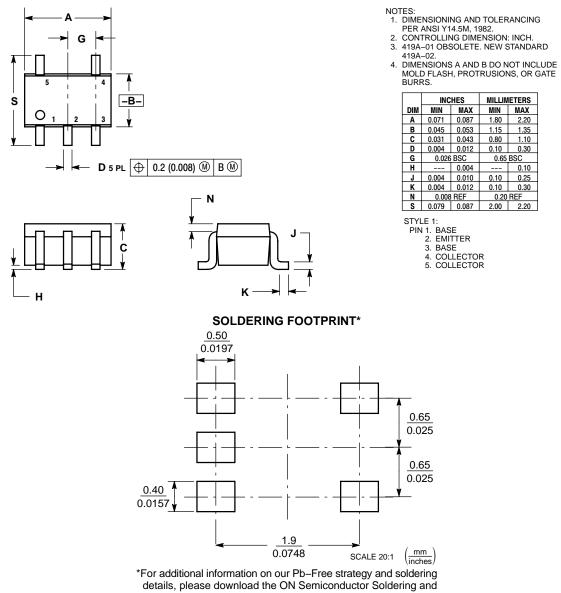


Figure 1. Derating Curve

#### NSB1706DMW5T1

#### PACKAGE DIMENSIONS

SC-88A, SOT-353, SC-70 CASE 419A-02 ISSUE J



Mounting Techniques Reference Manual, SOLDERRM/D.

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